

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1-7. (Canceled)

8. (Withdrawn) A method of fabricating a liquid crystal display device, comprising the steps of:

forming a first metal layer of a first metal on a substrate;

forming a second metal onto the first metal layer to form an alloy layer formed from an alloy including the first metal and a second metal disposed between the first metal and the second metal;

removing the second metal on the alloy layer;

patterning the first metal layer using a mask process to form a conductive line;

forming an insulating film having a contact hole on the alloy layer; and

forming a transparent electrode in electrical contact with the alloy layer via the contact hole.

9. (Withdrawn) The liquid crystal display device according to claim 8, wherein the first metal includes an aluminum-alloy.

10. (Withdrawn) The liquid crystal display device according to claim 8, wherein the first metal layer has a thickness of about 2000 to 3000Å.

11. (Withdrawn) The liquid crystal display device according to claim 8, wherein the second metal is one of molybdenum and chrome.

12. (Withdrawn) The liquid crystal display device according to claim 11, wherein the second metal has a thickness of about 100 to 500Å.

13. (Withdrawn) The liquid crystal display device according to claim 8, wherein said conductive line includes one of a gate line, a gate electrode, and a gate pad.

14. (Withdrawn) The liquid crystal display device according to claim 8, wherein said conductive line includes one of a data line, a source electrode, a drain electrode, and a data pad.

15. (Currently Amended) A liquid crystal display device, comprising:

a substrate;

a gate electrode disposed on the substrate;

a gate pad disposed on the substrate;

an insulating film disposed on the gate electrode and the gate pad;

an active layer disposed on the insulating film above the gate electrode;

an ohmic contact layer disposed on portions of the active layer;

a source electrode and a drain electrode disposed on the ohmic contact layer;

a passivation layer disposed on the source and drain electrodes;

a pixel electrode disposed on the passivation layer and contacting the drain electrode;

and

a transparent electrode disposed on the passivation layer and contacting the gate pad,

wherein the gate electrode and the gate pad both include a first layer formed of a first metal and an alloy layer formed on the surface of the first layer by heat generated by continuously depositing a second metal on the first metal, a residual of the second metal is

entirely removed so that the alloy layer of the gate pad is directly connected to the transparent electrode, and

wherein the first metal includes aluminum, and the alloy layer includes an alloy of aluminum and the second metal.

16. (Canceled)

17. (Currently Amended) The liquid crystal display device according to claim 15 [[16]], wherein the transparent electrode is disposed within a via formed through the passivation layer and insulating film.

18. (Original) The liquid crystal display device according to claim 15, wherein the passivation layer covers side surfaces of the source and drain electrodes.

19. (Original) The liquid crystal display device according to claim 15, wherein the passivation layer is disposed on the insulating film.

20. (Original) The liquid crystal display device according to claim 15, wherein the passivation layer contacts a portion of the active layer between the source and drain electrodes.

21. (New) A liquid crystal display device, comprising:  
a substrate;  
a gate electrode disposed on the substrate;  
a gate pad disposed on the substrate;  
an insulating film formed of a silicon oxide or a silicon nitride, and disposed on the gate electrode and the gate pad;

an active layer disposed on the insulating film above the gate electrode;

an ohmic contact layer disposed on portions of the active layer;

a source electrode and a drain electrode formed of one selected from a group consisting of MoW, MoTa and MoNb, and disposed on the ohmic contact layer;

a passivation layer formed of benzocyclobutene (BCB) or perfluorocyclobutane (PFCB), and disposed on the source and drain electrodes;

a pixel electrode disposed on the passivation layer and contacting the drain electrode;

and

a transparent electrode disposed on the passivation layer and contacting the gate pad,

wherein the gate electrode and the gate pad both include a AlNd layer, and a AlNd-Mo or a AlNd-Cr alloy layer formed on the surface of the AlNd layer, and the AlNd-Mo or the AlNd-Cr alloy layer is directly connected to the transparent electrode.